74LVT373 3.3 V octal D-type transparent latch; 3-state Rev. 3 – 21 November 2011

Product data sheet

1. General description

The 74LVT373 is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V. This device is an octal transparent latch coupled to eight 3-state output buffers. The two sections of the device are controlled independently by latch enable (LE) and output enable (\overline{OE}) control gates. The data on the Dn inputs are transferred to the latch outputs when the latch enable (LE) input is HIGH. The latch remains transparent to the data inputs while LE is HIGH, and stores the data that is present one setup time before the HIGH-to-LOW enable transition.

The 3-state output buffers are designed to drive heavily loaded 3-state buses, MOS memories, or MOS microprocessors. The active-low output enable (\overline{OE}) controls all eight 3-state buffers independent of the latch operation.

When \overline{OE} is LOW, the latched or transparent data appears at the outputs. When \overline{OE} is HIGH, the outputs are in the high-impedance OFF-state, which means they will neither drive nor load the bus.

The 74LVT373 is functionally identical to the 74LVT573, but has a different pin arrangement.

2. Features and benefits

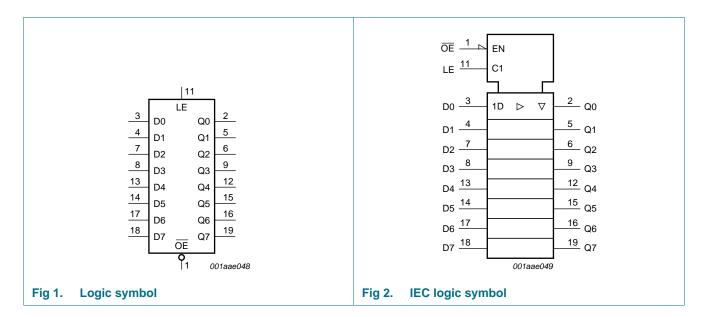
- Inputs and outputs arranged for easy interfacing to microprocessors
- 3-state outputs for bus interfacing
- Common output enable control
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Power-up reset
- Power-up 3-state
- Latch-up protection
 - JESD78 class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C

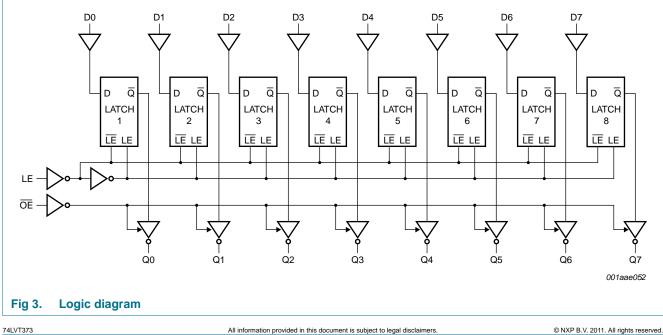


3. Ordering information

Table 1. Orde	Table 1. Ordering information								
Type number Package									
	Temperature range	Name	Description	Version					
74LVT373D	–40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1					
74LVT373PW	–40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1					

4. Functional diagram

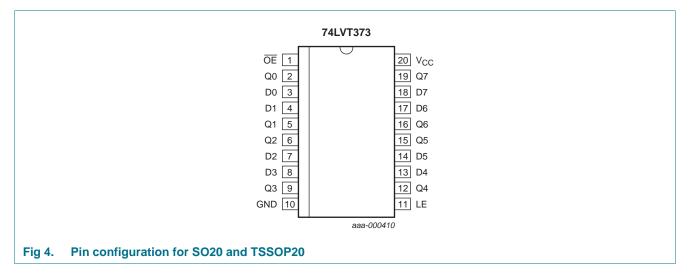




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5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
OE	1	output enable input (active LOW)
D0 to D7	3, 4, 7, 8, 13, 14, 17, 18	data input
GND	10	ground (0 V)
LE	11	latch enable (active HIGH)
Q0 to Q7	2, 5, 6, 9, 12, 15, 16, 19	data output
V _{CC}	20	supply voltage

6. Functional description

6.1 Function table

Table 3. Function table [1]

Operating mode	Control OE	Control LE	Input Dn	Internal regis	ster Output Qn
Load and read register	L	Н	L	L	L
enable			Н	Н	Н
Latch and read register	L	\downarrow	I	L	L
			h	Н	Н
Hold	L	L	Х	NC	NC
Disable outputs	Н	L	Х	NC	Z
		Н	Dn	Dn	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

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 \downarrow = HIGH-to-LOW latch enable transition;

h = HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition;

I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition;

Z = high-impedance OFF-state;

NC = no change;

X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-	-50	mA
I _{OK}	output clamping current	V _O < 0 V	-	-50	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-	-64	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[2] _	150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$	<u>[3]</u>	500	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] For SO20 packages: above 70 °C derate linearly with 8 mW/K. For TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-	-	-32	mA
l _{OL}	LOW-level output current		-	-	32	mA
		current duty cycle ≤ 50 %; $f_i \geq 1 \ kHz$	-	-	64	mA
T _{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

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9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter Conditions				–40 °C to +	85 °C	Unit
				Min	Typ[1]	Max	
∕ _{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = -18 mA		-1.2	-0.9	-	V
V _{OH}	HIGH-level output voltage	V _{CC} = 2.7 V to 3.6 V; I _{OH} = -100 μA		V _{CC} - 0.2	V _{CC} – 0.1	-	V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -8 \text{ mA}$		2.4	2.5	-	V
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -32 \text{ mA}$		2.0	2.2	-	V
/ _{OL}	LOW-level output voltage	V_{CC} = 2.7 V; I_{OL} = 100 μ A		-	0.1	0.2	V
		V _{CC} = 2.7 V; I _{OL} = 24 mA		-	0.3	0.5	V
		$V_{CC} = 3.0 \text{ V} \text{ I}_{OL} = 16 \text{ mA}$		-	0.25	0.4	V
		$V_{CC} = 3.0 \text{ V} \text{ I}_{OL} = 32 \text{ mA}$		-	0.3	0.5	V
		$V_{CC} = 3.0 \text{ V} \text{ I}_{OL} = 64 \text{ mA}$		-	0.4	0.55	V
/ _{OL(pu)}	power-up LOW-level output voltage	V_{CC} = 3.6 V; I_{O} = 1 mA; V _I = GND or V _{CC}	[2]	-	0.13	0.55	V
I	input leakage current	all input pins;					
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; \text{ V}_{I} = 5.5 \text{ V}$		-	1	10	μA
		control pins;					
		V_{CC} = 3.6 V; V_{CC} or GND		-	±0.1	±1	μA
		data pins					
		$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = V_{CC}$	[3]	-	0.1	1	μA
		$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = 0 \text{ V}$		-5	-1	-	μA
OFF	power-off leakage current	V_{CC} = 0 V; V_{I} or V_{O} = 0 V to 4.5 V		-	1	±100	μΑ
BHL	bus hold LOW current	Dn input; V_{CC} = 3 V; V_I = 0.8 V	[4]	75	150	-	μA
внн	bus hold HIGH current	Dn input; V_{CC} = 3 V; V_I = 2.0 V		-	-150	-75	μA
BHHO	bus hold HIGH overdrive current	Dn input; $V_{CC} = 3.6 \text{ V}$; $V_I = 0 \text{ V}$ to 3.6 V	<u>[4]</u>	-	-	500	μA
BHLO	bus hold LOW overdrive current	Dn input; $V_{CC} = 3.6 \text{ V}$; $V_I = 0 \text{ V}$ to 3.6 V		-500	-	-	μA
LO	output leakage current	Qn output HIGH when V_{O} = 5.5 V and V_{CC} = 3.0 V		-	60	125	μA
O(pu/pd)	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V}; V_O = \underline{0.5} \text{ V to } V_{CC};$ $V_I = \text{GND or } V_{CC}; \overline{\text{OE}} = \text{don't care}$		-	1	±100	μA
OZ	OFF-state output current	V_{CC} = 3.6 V; V_{I} = V_{IH} or V_{IL}					
		output HIGH: $V_0 = 3.0 V$		-	1	5	μΑ
		output LOW: $V_0 = 0.5 V$		-5	-1	-	μΑ
СС	supply current	V_{CC} = 3.6 V; V_{I} = GND or $V_{CC};$ I_{O} = 0 A					
		outputs HIGH		-	0.13	0.19	mA
		outputs LOW		-	3	12	mA
		outputs disabled	[6]	-	0.13	0.19	mA

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Symbol	Parameter	Conditions	Conditions		T _{amb} = -40 °C to +85 °C		
				Min	Typ <mark>[1]</mark>	Max	
ΔI_{CC}	additional supply current	per input pin; $V_{CC} = 3 \text{ V}$ to 3.6 V; one input at $V_{CC} - 0.6 \text{ V}$ and other inputs at V_{CC} or GND	[7]	-	0.1	0.2	mA
CI	input capacitance	$V_I = 0 V \text{ or } 3.0 V$		-	4	-	pF
Co	output capacitance	outputs disabled; $V_0 = 0 V$ or 3.0 V		-	8	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

- [3] Unused pins at V_{CC} or GND.
- [4] This is the bus hold overdrive current required to force the input to the opposite logic state.
- [5] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.
- [6] I_{CC} is measured with outputs pulled to V_{CC} or GND.
- [7] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7.Dynamic characteristics

Voltages are referenced to ground (GND = 0 V); for test circuit see <u>Figure 10</u>.

Symbol	Parameter	Conditions	T _{amb} :	= –40 °C to	+85 °C	Unit
			Min	Typ[1]	Max	
t _{PLH}	LOW to HIGH	LE to Qn; see Figure 5				
	propagation delay	V_{CC} = 3.0 V to 3.6 V	1.9	3.1	4.9	ns
		$V_{CC} = 2.7 V$	2.6	3.7	5.3	ns
		Dn to Qn; see Figure 6				
		V_{CC} = 3.0 V to 3.6 V	1.9	3.0	4.8	ns
		$V_{CC} = 2.7 V$	2.6	3.4	5.2	ns
t _{PHL}	HIGH to LOW	LE to Qn; see Figure 5				
	propagation delay	V_{CC} = 3.0 V to 3.6 V	1.9	3.3	4.7	ns
		$V_{CC} = 2.7 V$	1.9	3.4	5.0	ns
		Dn to Qn; see Figure 6				
		V_{CC} = 3.0 V to 3.6 V	1.8	3.0	4.8	ns
		$V_{CC} = 2.7 V$	2.4	3.6	5.0	ns
t _{PZH}	OFF-state to HIGH	OE to Qn; see Figure 7				
	propagation delay	V_{CC} = 3.0 V to 3.6 V	1.8	3.4	5.7	ns
		$V_{CC} = 2.7 V$	3.0	4.5	6.0	ns
t _{PZL}	OFF-state to LOW	OE to Qn; see Figure 8				
	propagation delay	V_{CC} = 3.0 V to 3.6 V	1.9	3.3	5.3	ns
		$V_{CC} = 2.7 V$	2.7	4.0	5.6	ns

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Symbol	Parameter Conditions			T _{amb} :	= –40 °C to	+85 °C	Unit
			-	Min	Typ <mark>[1]</mark>	Max	_
t _{PHZ}	HIGH to OFF-state	OE to Qn; see Figure 7					
propagation delay	V_{CC} = 3.0 V to 3.6 V		1.8	3.2	5.1	ns	
	$V_{CC} = 2.7 V$		1.9	3.5	5.3	ns	
t _{PLZ} LOW to OFF-state		OE to Qn; see Figure 8					
propagation delay	V_{CC} = 3.0 V to 3.6 V		2.1	3.2	4.6	ns	
	$V_{CC} = 2.7 V$		2.0	3.0	4.6	ns	
t _{su} set-up time	Dn to LE; see Figure 9	[2]					
		V_{CC} = 3.0 V to 3.6 V		1.1	-	-	ns
		$V_{CC} = 2.7 V$		1.0	-	-	ns
t _h	hold time	Dn to LE; see Figure 9	<u>[3]</u>				
		V_{CC} = 3.0 V to 3.6 V		1.4	-	-	ns
		$V_{CC} = 2.7 V$		1.4	-	-	ns
t _W	pulse width	LE input HIGH; see Figure 5	[4]				
		V_{CC} = 3.0 V to 3.6 V		3.0	-	-	ns
		$V_{CC} = 2.7 V$		3.0	-	-	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to ground (GND = 0 V); for test circuit see <u>Figure 10</u>.

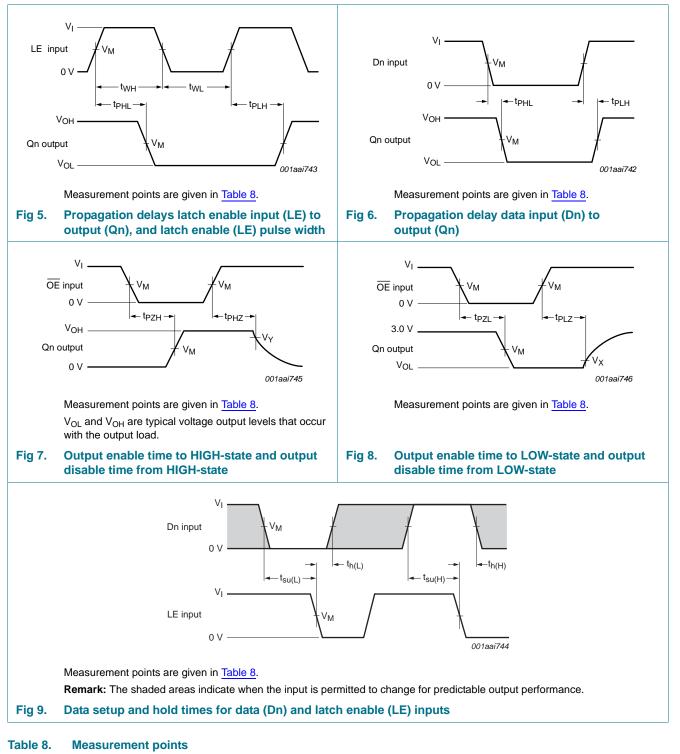
[1] Typical values are measured at T_{amb} = 25 $^{\circ}C$ and V_{CC} = 3.3 V and 2.7 V respectively.

 $\label{eq:theta} [3] \quad t_h \text{ is the same as } t_{h(L)} \text{ and } t_{h(H)}.$

 $\label{eq:twisted} [4] \quad t_W \text{ is the same as } t_{WL} \text{ and } t_{WH}.$

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11. Waveforms



Input	Output		
V _M	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$

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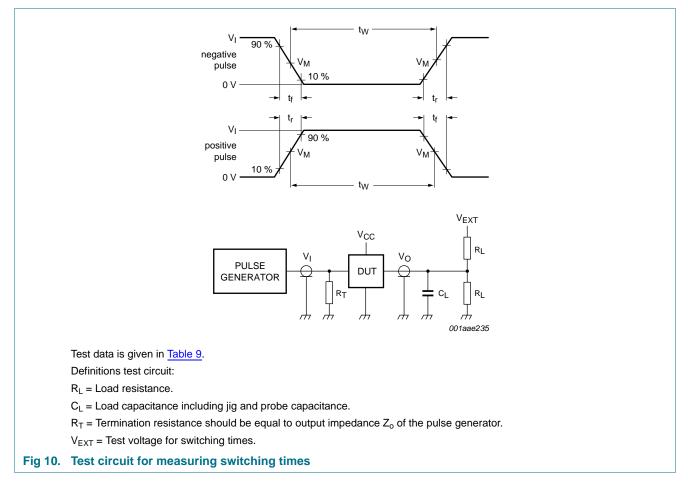


Table 9. Test data

Input	Input			Load V _E		V _{EXT}		
VI	fi	tw	t _r , t _f	CL	RL	t _{PHZ} , t _{PZH}	t _{PLZ} , t _{PZL}	t _{PLH} , t _{PHL}
2.7 V	\leq 10 MHz	500 ns	\leq 2.5 ns	50 pF	500 Ω	GND	6 V	open

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12. Package outline

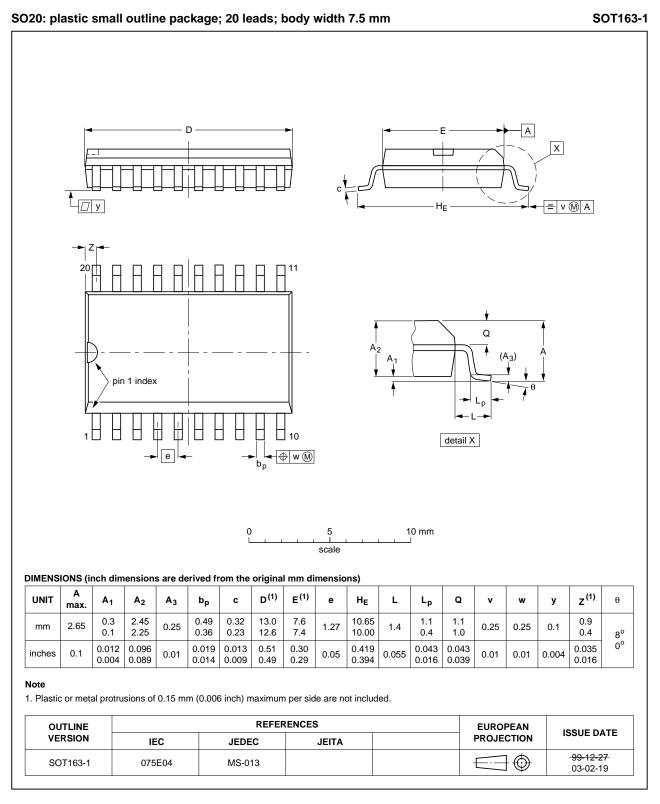


Fig 11. Package outline SOT163-1 (SO20)

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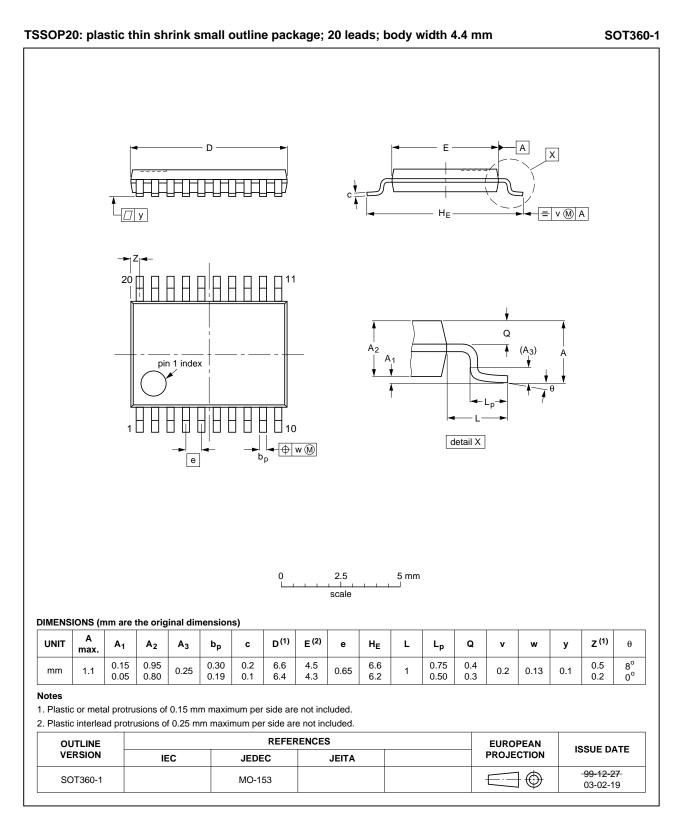


Fig 12. Package outline SOT360-1 (TSSOP20)

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13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVT373 v.3	20111121	Product data sheet	-	74LVT373 v.2	
Modifications:	 Legal pages 	updated.			
74LVT373 v.2	20110916	Product data sheet	-	74LVT373 v.1	
74LVT373 v.1	19930701	Product data sheet	-	-	

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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